Low Voltage Single Supply Dual DPDT Analog Switch

The NLAS9431 is an advanced dual–independent CMOS double pole–double throw (DPDT) analog switch fabricated with silicon gate CMOS technology. It achieves high speed propagation delays and low ON resistances while maintaining CMOS low power dissipation. This DPDT controls analog and digital voltages that may vary across the full power–supply range (from $V_{\rm CC}$ to GND).

The device has been designed so the ON resistance (R_{ON}) is much lower and more linear over input voltage than R_{ON} of typical CMOS analog switches.

The channel select input is compatible with standard CMOS outputs. The channel select input structure provides protection when voltages between 0 V and 5.5 V are applied, regardless of the supply voltage. This input structure helps prevent device destruction caused by supply voltage – input/output voltage mismatch, battery backup, hot insertion, etc.

The NLAS9431 can also be used as a quad 2-to-1 multiplexer-demultiplexer analog switch with two Select pins that each controls two multiplexer-demultiplexers.

- Direct Battery Connection
- Channel Select Input Over-Voltage Tolerant to 5.5 V
- Fast Switching and Propagation Speeds
- Break-Before-Make Circuitry
- Low Power Dissipation: $I_{CC} = 2 \mu A \text{ (Max)}$ at $T_A = 25^{\circ}\text{C}$
- Diode Protection Provided on Channel Select Input
- Improved Linearity and Lower ON Resistance over Input Voltage
- Latch-up Performance Exceeds 300 mA
- Chip Complexity: 158 FETs
- 16-Lead WQFN Package, 1.8 mm x 2.6 mm
- This is a Pb-Free Device



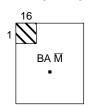
ON Semiconductor®

http://onsemi.com

MARKING DIAGRAMS



WQFN16 CASE 488AP



BA = Specific Device Code

M = Date Code & Assembly Location

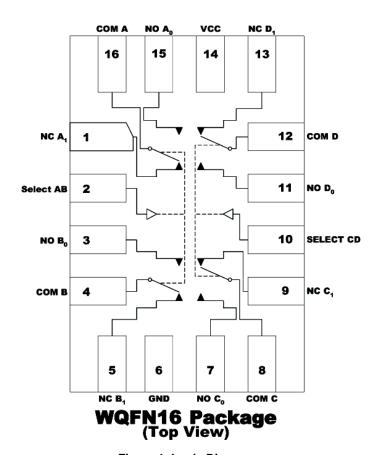
= Pb-Free Device

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 10 of this data sheet.

FUNCTION TABLE

Select AB or CD	On Channel
L	NC to COM
H	NO to COM



SELECT AB -

Figure 1. Logic Diagram

Figure 2. IEC Logic Symbol

MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V _{CC}	Positive DC Supply Voltage	-0.5 to +7.0	V
V _{IS}	Analog Input Voltage (V _{NO} or V _{COM})	$-0.5 \le V_{\text{IS}} \le V_{\text{CC}} + 0.5$	
V _{IN}	Digital Select Input Voltage	$-0.5 \le V_{\parallel} \le +7.0$	V
I _{IK}	DC Current, Into or Out of Any Pin	±50	mA
P _D	Power Dissipation in Still Air	800	mW
T _{STG}	Storage Temperature Range	-65 to +150	°C
TL	Lead Temperature, 1 mm from Case for 10 Seconds	260	°C
TJ	Junction Temperature Under Bias	+150	°C
MSL	Moisture Sensitivity	Level 1	
F _R	Flammability Rating Oxygen Index: 30% – 35%	UL 94-V0 (0.125 in)	
I _{Latch-Up}	Latch–Up Performance Above V _{CC} and Below GND at 125°C (Note 1)	±300	mA
θ_{JA}	Thermal Resistance	80	°C/W

Maximum Ratings are those values beyond which damage to the device may occur. Exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute—maximum—rated conditions is not implied. Functional operation should be restricted to the Recommended Operating Conditions.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Min	Max	Unit	
V _{CC}	DC Supply Voltage	2.0	5.5	V	
V _{IN}	Digital Select Input Voltage	GND	5.5	V	
V _{IS}	Analog Input Voltage (NC, NO, COM)	GND	V _{CC}	V	
T _A	Operating Temperature Range	-55	+125	°C	
t _r , t _f	Input Rise or Fall Time, SELECT VCC	$c = 3.3 \text{ V} \pm 0.3 \text{ V}$ $c = 5.0 \text{ V} \pm 0.5 \text{ V}$	0	100 20	ns/V

DEVICE JUNCTION TEMPERATURE VERSUS TIME TO 0.1% BOND FAILURES

Junction Temperature °C	Time, Hours	Time, Years
80	1,032,200	117.8
90	419,300	47.9
100	178,700	20.4
110	79,600	9.4
120	37,000	4.2
130	17,800	2.0
140	8,900	1.0

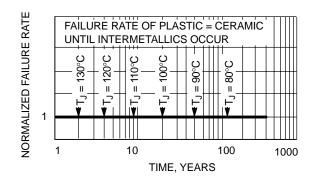


Figure 3. Failure Rate vs. Time Junction Temperature

^{1.} Tested to EIA/JESD78.

DC CHARACTERISTICS – Digital Section (Voltages Referenced to GND)

				Guaran			
Symbol	Parameter	Condition	V _{CC}	-55°C to 25°C	<85°C	<125°C	Unit
V _{IH}	Minimum High-Level Input		2.0	1.5	1.5	1.5	V
	Voltage, Select Inputs		2.5	1.9	1.9	1.9	
			3.0	2.1	2.1	2.1	
			4.5	3.15	3.15	3.15	
			5.5	3.85	3.85	3.85	
V _{IL}	Maximum Low-Level Input		2.0	0.5	0.5	0.5	V
	Voltage, Select Inputs		2.5	0.6	0.6	0.6	
			3.0	0.9	0.9	0.9	
			4.5	1.35	1.35	1.35	
			5.5	1.65	1.65	1.65	
I _{IN}	Maximum Input Leakage Current	V _{IN} = 5.5 V or GND	5.5	±0.2	±2.0	±2.0	μΑ
l _{OFF}	Power Off Leakage Current, Select Inputs	V _{IN} = 5.5 V or GND	0	±10	±10	±10	μΑ
Icc	Maximum Quiescent Supply Current	Select and V _{IS} = V _{CC} or GND	5.5	4.0	4.0	8.0	μΑ

DC ELECTRICAL CHARACTERISTICS - Analog Section

				Guaranteed Limit			
Symbol	Parameter	Condition	V _{CC}	-55°C to 25°C	<85°C	<125°C	Unit
R _{ON}	Maximum "ON" Resistance (Figures 17 – 23)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{IS} = \text{GND to } V_{CC}$ $I_{IN}I \leq 10.0 \text{ mA}$		85 45 30	95 50 35	105 55 40	Ω
			5.5	25	30	35	
R _{FLAT (ON)}	ON Resistance Flatness (Figures 17 – 23)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $I_{IN}I \le 10.0 \text{ mA}$ $V_{IS} = 1 \text{ V, 2 V, 3.5 V}$	4.5	4	4	5	Ω
I _{NC(OFF)} I _{NO(OFF)}	NO or NC Off Leakage Current (Figure 9)	$V_{IN} = V_{IL} \text{ or } V_{IH}$ $V_{NO} \text{ or } V_{NC} = 1.0 \text{ V}_{COM} 4.5 \text{ V}$	5.5	1	10	100	nA
I _{COM(ON)}	COM ON Leakage Current (Figure 9)	$\begin{aligned} & V_{IN} = V_{IL} \text{ or } V_{IH} \\ & V_{NO} \text{ 1.0 V or } 4.5 \text{ V with } V_{NC} \text{ floating or } \\ & V_{NO} \text{ 1.0 V or } 4.5 \text{ V with } V_{NO} \text{ floating } \\ & V_{COM} = 1.0 \text{ V or } 4.5 \text{ V} \end{aligned}$	5.5	1	10	100	nA

AC ELECTRICAL CHARACTERISTICS (Input $t_r = t_f = 3.0 \text{ ns}$)

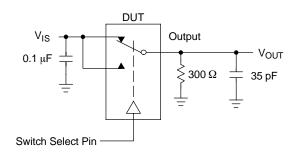
					Guaranteed Maximum Limit							
			v _{cc}	V _{IS}	- 55	5°C to 2	25°C	<8	5°C	<12	25°C	
Symbol	Parameter	Test Conditions	(V)	(V)	Min	Тур*	Max	Min	Max	Min	Max	Unit
t _{ON}	Turn-On Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	5	23	35	5	38	5	41	ns
	(Figures 12 and 13)	(Figures 5 and 6)	3.0	2.0	5	16	24	5	27	5	30	
			4.5	3.0	2	11	16	2	19	2	22	
			5.5	3.0	2	9	14	2	17	2	20	
t _{OFF}	Turn-Off Time	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	1	7	12	1	15	1	18	ns
	(Figures 12 and 13)	(Figures 5 and 6)	3.0	2.0	1	5	10	1	13	1	16	
			4.5	3.0	1	4	6	1	9	1	12	
			5.5	3.0	1	3	5	1	8	1	11	
t _{BBM}	Minimum Break-Before-Make	$R_L = 300 \Omega, C_L = 35 pF$	2.5	2.0	1	12		1		1		ns
	Time	(Figure 4)	3.0	2.0	1	11		1		1		
			4.5	3.0	1	6		1		1		
			5.5	3.0	1	5		1		1		

		Typical @ 25, V _{CC} = 5.0 V	~F
C _{IN}	Maximum Input Capacitance, Select Input	8	pF
C _{NO} or C _{NC}	Analog I/O (switch off)	10	
C _{COM}	Common I/O (switch off)	10	
C _(ON)	Feedthrough (switch on)	20	

^{*}Typical Characteristics are at 25°C.

ADDITIONAL APPLICATION CHARACTERISTICS (Voltages Referenced to GND Unless Noted)

			Vcc	Typical	
Symbol	Parameter	Parameter Condition		25°C	Unit
BW	Maximum On-Channel -3dB	V _{IS} = 0 dBm	3.0	145	MHz
	Bandwidth or Minimum Frequency Response (Figure 11)	V _{IS} centered between V _{CC} and GND	4.5	170	
	Response (Figure 11)	(Figure 7)	5.5	175	
V _{ONL}	Maximum Feedthrough On Loss	V _{IS} = 0 dBm @ 100 kHz to 50 MHz	3.0	-3	dB
		V _{IS} centered between V _{CC} and GND	4.5	-3	
		(Figure 7)	5.5	-3	
V _{ISO}	Off-Channel Isolation (Figure 10)	f = 100 kHz; V _{IS} = 1 V RMS	3.0	-93	dB
		V _{IS} centered between V _{CC} and GND	4.5	-93	
		(Figure 7)	5.5	-93	
Q	Charge Injection Select Input to	V _{IS} = V _{CC to} GND, F _{IN} = 20 kHz			рС
	Common I/O (Figure 15)	$t_r = t_f = 3 \text{ ns}$	3.0	1.5	
		$R_{IS} = 0 \Omega$, $C_L = 1000 pF$	5.5	3.0	
		$Q = C_L * \Delta V_{OUT}$			
		(Figure 8)			
THD	Total Harmonic Distortion THD +	F_{IN} = 20 Hz to 100 kHz, R_L = Rgen = 600 Ω , C_L = 50 pF			%
	Noise (Figure 14)	$V_{IS} = 5.0 V_{PP}$ sine wave	5.5	0.1	
VCT	Channel-to-Channel Crosstalk	f = 100 kHz; V _{IS} = 1 V RMS			dB
		V _{IS} centered between V _{CC} and GND	5.5	-90	
		(Figure 7)	3.0	-90	



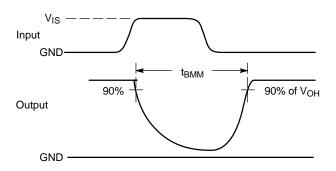
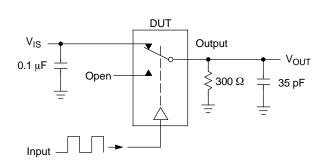


Figure 4. t_{BBM} (Time Break-Before-Make)



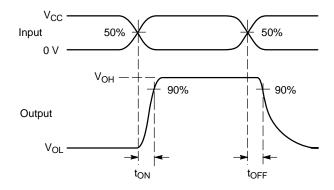
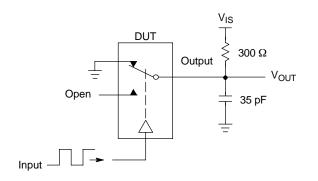


Figure 5. t_{ON}/t_{OFF}



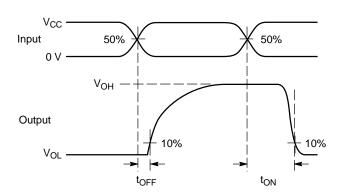
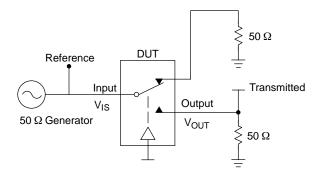


Figure 6. t_{ON}/t_{OFF}



Channel switch control/s test socket is normalized. Off isolation is measured across an off channel. On loss is the bandwidth of an On switch. V_{ISO} , Bandwidth and V_{ONL} are independent of the input signal direction.

$$\begin{split} &V_{ISO} = \text{Off Channel Isolation} = 20 \text{ Log } \left(\frac{V_{OUT}}{V_{IS}}\right) \text{for } V_{IN} \text{ at } 100 \text{ kHz} \\ &V_{ONL} = \text{On Channel Loss} = 20 \text{ Log } \left(\frac{V_{OUT}}{V_{IS}}\right) \text{for } V_{IN} \text{ at } 100 \text{ kHz to } 50 \text{ MHz} \end{split}$$

Bandwidth (BW) = the frequency 3 dB below V_{ONL} V_{CT} = Use V_{ISO} setup and test to all other switch analog input/outputs terminated with 50 Ω

Figure 7. Off Channel Isolation/On Channel Loss (BW)/Crosstalk (On Channel to Off Channel)/V_{ONL}

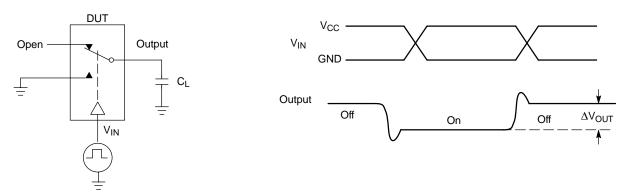


Figure 8. Charge Injection: (Q)

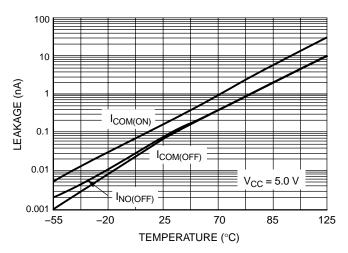
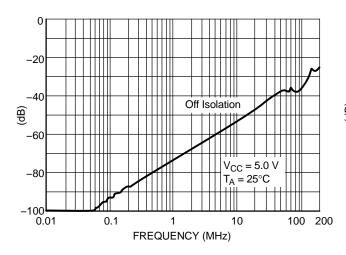


Figure 9. Switch Leakage vs. Temperature

30



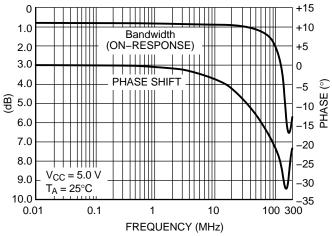
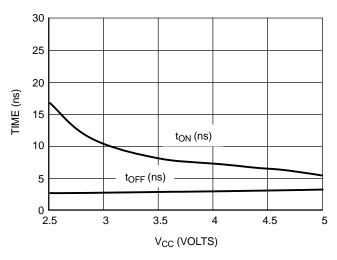


Figure 10. Off-Channel Isolation

Figure 11. Typical Bandwidth and Phase Shift



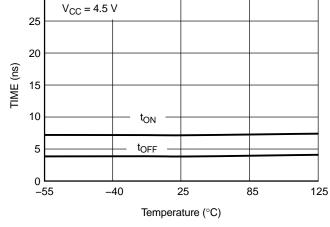
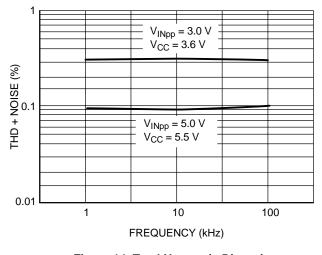


Figure 12. t_{ON} and t_{OFF} vs. V_{CC} at 25°C

Figure 13. t_{ON} and t_{OFF} vs. Temp



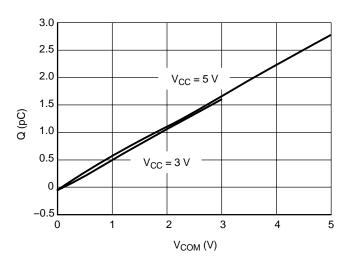
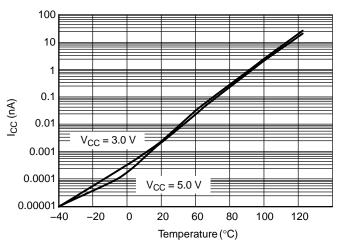


Figure 14. Total Harmonic Distortion Plus Noise vs. Frequency

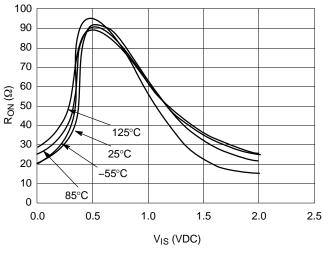
Figure 15. Charge Injection vs. COM Voltage



100 $V_{CC} = 2.0 \text{ V}$ 80 60 R_{ON} (Ω) $V_{CC} = 2.5 \text{ V}$ 40 $V_{CC} = 3.0 \text{ V}$ $V_{CC} = 4.0 \text{ V}$ 20 $V_{CC} = 5.5 \text{ V}$ 0.0 1.0 2.0 3.0 4.0 5.0 6.0 V_{IS} (VDC)

Figure 16. I_{CC} vs. Temp, V_{CC} = 3 V & 5 V

Figure 17. R_{ON} vs. V_{CC}, Temp = 25°C



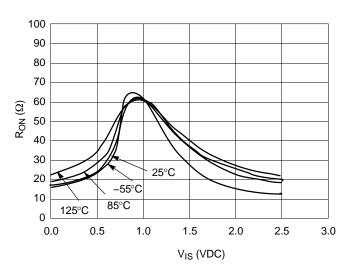
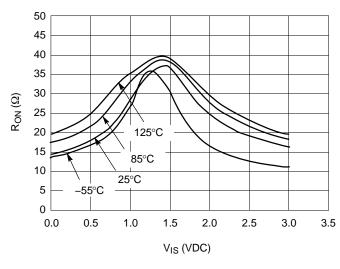


Figure 18. R_{ON} vs Temp, $V_{CC} = 2.0 \text{ V}$

Figure 19. R_{ON} vs. Temp, V_{CC} = 2.5 V



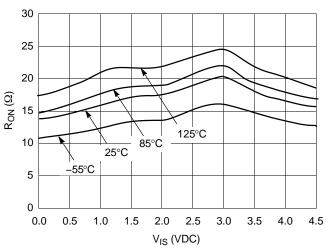
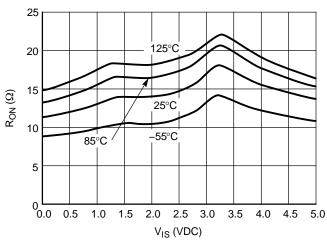


Figure 20. R_{ON} vs. Temp, V_{CC} = 3.0 V

Figure 21. R_{ON} vs. Temp, $V_{CC} = 4.5 \text{ V}$



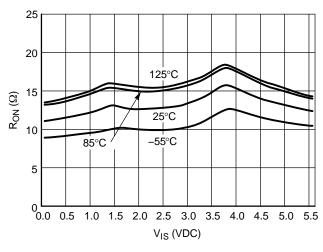


Figure 22. R_{ON} vs. Temp, V_{CC} = 5.0 V

Figure 23. R_{ON} vs. Temp, V_{CC} = 5.5 V

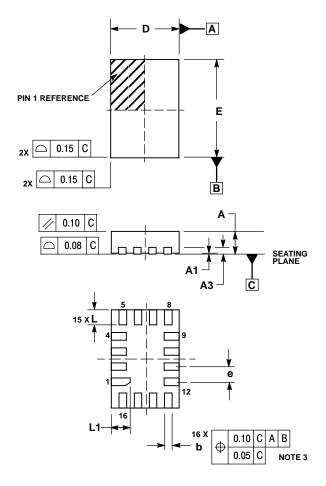
DEVICE ORDERING INFORMATION

Device Nomenclature							
Device	Circuit Indicator	Technology	Device Function	Package Suffix	Tape & Reel Suffix	Package Type	Shipping [†]
NLAS9431MTR2G	NL	AS	9431	MT	R2	WQFN16 (Pb-Free)	3000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D. *This package is inherently Pb–Free.

PACKAGE DIMENSIONS

WQFN16 MN SUFFIX CASE 488AP-01 ISSUE A



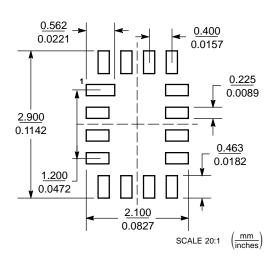
NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- DIMENSION & APPLIES TO PLATED TERMINAL AND IS MEASURED BETWEEN 0.25 AND 0.30 MM FROM TERMINAL
- 4. COPLANARITY APPLIES TO THE EXPOSED PAD AS WELL AS THE TERMINALS
- AS WELL AS THE TERMINALS.

 5. EXPOSED PADS CONNECTED TO DIE FLAG.
 USED AS TEST CONTACTS.

	MILLIMETERS				
DIM	MIN	MAX			
Α	0.70	0.80			
A1	0.00	0.050			
A3	0.20 REF				
b	0.15	0.25			
D	1.80	BSC			
Е	2.60	BSC			
е	0.40	BSC			
L	0.30	0.50			
L1	0.40	0.60			

MOUNTING FOOTPRINT



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